

2N5050-2N5052

High-reliability discrete products and engineering services since 1977

NPN SILICON HIGH POWER TRANSISTORS

NFEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

MAXIMUM RATINGS

| Ratings | Symbol | 2N5050 | 2N5051 | 2N5052 | Unit |
|---|-----------|-------------|--------|--------|------|
| Collector-Emitter Voltage | Vceo | 125 | 150 | 200 | Vdc |
| Collector-Base Voltage | Vcbo | 125 | 150 | 200 | Vdc |
| Emitter-Base Voltage | Vebo | 7.0 | | | Vdc |
| Collector Current | lc | 2.0 | | | Adc |
| Total Power Dissipation $T_c = 25^{\circ}C$ | PD | 40 | | | w |
| Junction Temperature | ۲ı | 150 | | | °C |
| Storage Junction Temperature Range | T_{stg} | -65 to +200 | | | °C |
| Maximum Thermal Resistance Junction to Case | Rejc | | 7.0 | | °C/W |

ELECTRICAL CHARACTERSITICS (T_A = 25°C unless otherwise specified)

| Characteristics | | Symbol | Min. | Max. | Unit |
|--|--------|-----------------------|------|------|--------|
| OFF CHARACTERISTICS | | | | | |
| Collector-Emitter Sustaining Voltage | 2N5050 | | 125 | - | |
| $I_{C} = 10 mA$, $I_{B} = 0$ | 2N5051 | V _{CEO(sus)} | 150 | - | Vdc |
| | 2N5052 | | 200 | - | |
| Collector-Emitter Saturation Voltage | | V _{CE(sat)} | | | Vdc |
| $I_C = 2Adc$, $I_B = -0.5 Adc$ | | V CE(sat) | - | 1.2 | vac |
| Collector-Base Saturation Voltage | | N | | | Vdc |
| $I_{C} = 2Adc, I_{B} = -0.5 Adc$ | | $V_{BE(sat)}$ | - | 1.5 | Vac |
| Base-Emitter On-Voltage | | N | | | Vala |
| I _C = 750mAdc, V _{CE} = 5Vdc | | V _{BE(ON)} | - | 1.2 | Vdc |
| Collector Cutoff Current | | | | | |
| V _{CE} = 125Vdc, I _B = 0 | 2N5050 | ICEO | - | - | mAdc |
| $V_{CE} = 150Vdc, I_{B} = 0$ | 2N5051 | ICEO | - | 5.0 | mauc |
| $V_{CE} = 200 V dc$, $I_B = 0$ | 2N5052 | | - | - | |
| Collector Cutoff Current | | Ісво | | | mAdc |
| V_{CB} = Rated V_{CBO} , I_E = 0 | | ICBO | - | 0.1 | mAde |
| Emitter Cutoff Current | | | | | mAdc |
| $V_{EB} = 7Vdc$, $I_{C} = 0$ | | I _{EBO} | - | 1.0 | made |
| DC Current Gain | | h | | | |
| Ic = 750mAdc, V _{CE} = 5.0 Vdc | | h _{FE} | 25 | 100 | - |
| Transition Frequency | | f⊤ | 10/ | typ) | MHz |
| I_{C} = 500mAdc, V_{CE} = 10Vdc, f = 1MHz | | | 10(| (14) | 141112 |



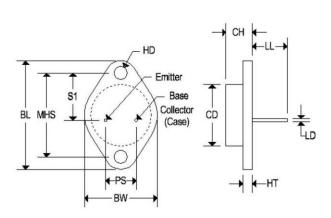
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MECHANICAL CHARACTERISTICS

| Case | TO-66 | |
|----------|---------------|--|
| Marking | Alpha-numeric | |
| Polarity | See below | |



| | TO-66 | | | | | |
|-----|-------|-------|-------------|--------|--|--|
| Dim | Inc | hes | Millimeters | | | |
| | Min | Max | Min | Мах | | |
| BL | 1.205 | 1.280 | 30.60 | 32.50 | | |
| CD | 0.445 | 0.557 | 11.303 | 14.148 | | |
| СН | 0.257 | 0.284 | 6.540 | 7.220 | | |
| LL | 0.374 | 0.413 | 9.500 | 10.50 | | |
| BW | 0.680 | 0.727 | 17.26 | 18.46 | | |
| LD | 0.030 | 0.036 | 0.760 | 0.920 | | |
| HT | 0.054 | 0.065 | 1.380 | 1.650 | | |
| MHS | 0.951 | 0.976 | 24.16 | 24.78 | | |
| S1 | 0.545 | 0.614 | 13.84 | 15.60 | | |
| HD | 0.131 | 0.154 | 3.320 | 3.920 | | |
| PS | 0.191 | 0.210 | 4.860 | 5.340 | | |